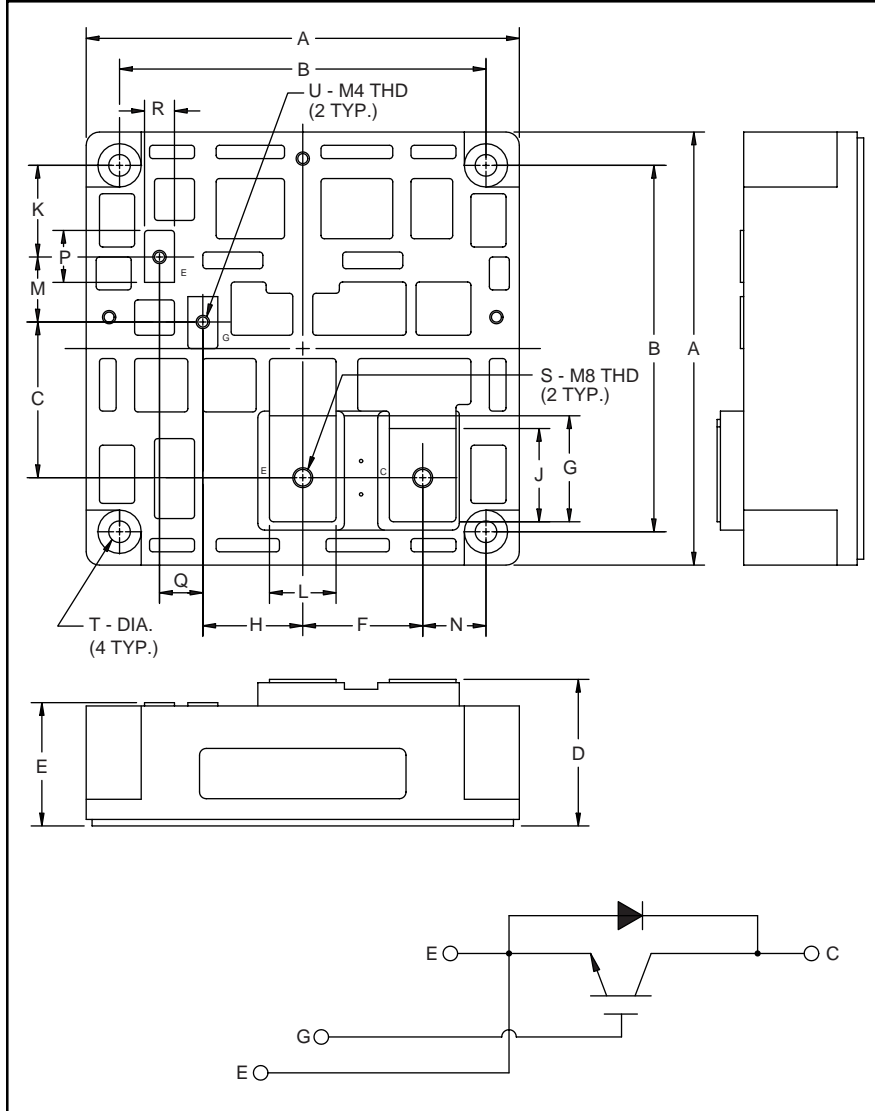


Single IGBTMOD™ H-Series Module 1200 Amperes/1200 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	5.12	130.0
B	4.33±0.01	110.0±0.25
C	1.840	46.75
D	1.73±0.04/0.02	44.0±1.0/0.5
E	1.46±0.04/0.02	37.0±1.0/0.5
F	1.42	36.0
G	1.25	31.8
H	1.18	30.0
J	1.10	28.0
K	1.08	27.5

Dimensions	Inches	Millimeters
L	0.79	20.0
M	0.77	19.5
N	0.75	19.0
P	0.61	15.6
Q	0.51	13.0
R	0.35	9.0
S	M8 Metric	M8
T	0.26 Dia.	Dia. 6.5
U	M4 Metric	M4



Description:

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of one IGBT Transistor in a single configuration with a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- Low Drive Power
- Low $V_{CE(sat)}$
- Discrete Super-Fast Recovery Free-Wheel Diode
- Isolated Baseplate for Easy Heat Sinking

Applications:

- AC Motor Control
- Motion/Servo Control
- UPS
- Welding Power Supplies
- Laser Power Supplies

Ordering Information:

Example: Select the complete part module number you desire from the table below -i.e. CM1200HA-24J is a 1200V (V_{CES}), 1200 Ampere Single IGBTMOD™ Power Module.

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	1200	24

CM1200HA-24J
Single IGBTMOD™ H-Series Module
 1200 Amperes/1200 Volts

Absolute Maximum Ratings, $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified

Ratings	Symbol	CM1200HA-24J	Units
Junction Temperature	T_j	-40 to +150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to +125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E SHORT)	V_{CES}	1200	Volts
Gate-Emitter Voltage (C-E SHORT)	V_{GES}	± 20	Volts
Collector Current ($T_c = 25^\circ\text{C}$)	I_C	1200	Amperes
Peak Collector Current ($T_j \leq 150^\circ\text{C}$)	I_{CM}	2400*	Amperes
Emitter Current** ($T_c = 25^\circ\text{C}$)	I_E	1200	Amperes
Peak Emitter Current** ($T_j \leq 150^\circ\text{C}$)	I_{EM}	2400*	Amperes
Maximum Collector Dissipation ($T_c = 25^\circ\text{C}$) ($T_j < 150^\circ\text{C}$)	P_C	5800	Watts
Max. Mounting Torque M8 Terminal Screws	-	95	in-lb
Max. Mounting Torque M6 Mounting Screws	-	26	in-lb
Mounting Torque G(E) Terminal M4	-	15	in-lb
Module Weight (Typical)	-	1600	Grams
Isolation Voltage, Main Terminal to Base Plate, AC 1 Min.	V_{iso}	2500	Volts

Static Electrical Characteristics, $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0V$	-	-	6	mA
Gate Leakage Current	I_{GES}	$V_{GE} = V_{CES}, V_{CE} = 0V$	-	-	0.5	μA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 120\text{mA}, V_{CE} = 10V$	4.5	6.0	7.5	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 1200\text{A}, V_{GE} = 15V, T_j = 25^\circ\text{C}$	-	2.4	3.1	Volts
		$I_C = 1200\text{A}, V_{GE} = 15V, T_j = 125^\circ\text{C}$	-	2.5	-	Volts
Total Gate Charge	Q_G	$V_{CC} = 600V, I_C = 1200\text{A}, V_{GE} = 15V$	-	5000	-	nC
Emitter Current Voltage**	V_{EC}	$I_E = 1200\text{A}, V_{GE} = 0V$	-	-	3.7	Volts

Dynamic Electrical Characteristics, $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units	
Input Capacitance	C_{ies}		-	-	200	nF	
Output Capacitance	C_{oes}	$V_{GE} = 0V, V_{CE} = 10V$	-	-	70	nF	
Reverse Transfer Capacitance	C_{res}		-	-	40	nF	
Resistive	Turn-on Delay Time	$t_{d(on)}$	$V_{CC} = 600V, I_C = 1200\text{A},$	-	-	600	ns
Load	Rise Time	t_r	$V_{GE1} = V_{GE2} = 15V,$	-	-	1800	ns
Switching	Turn-off Delay Time	$t_{d(off)}$	$R_G = 3.3\Omega, \text{Resistive}$	-	-	1200	ns
Time	Fall Time	t_f	Load Switching Operation	-	-	1500	ns
Diode Reverse Recovery Time**	t_{rr}	$I_E = 1200\text{A}, di_E/dt = -2400\text{A}/\mu\text{s}$	-	-	300	ns	
Diode Reverse Recovery Charge**	Q_{rr}	$I_E = 1200\text{A}, di_E/dt = -2400\text{A}/\mu\text{s}$	-	9.0	-	μC	

Thermal and Mechanical Characteristics, $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case**	$R_{th(j-c)Q}$	Per IGBT	-	-	0.022	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case**	$R_{th(j-c)R}$	Per FWDi	-	-	0.050	$^\circ\text{C}/\text{W}$
Contact Thermal Resistance	$R_{th(c-f)}$	Per Module, Thermal Grease Applied	-	-	0.018	$^\circ\text{C}/\text{W}$

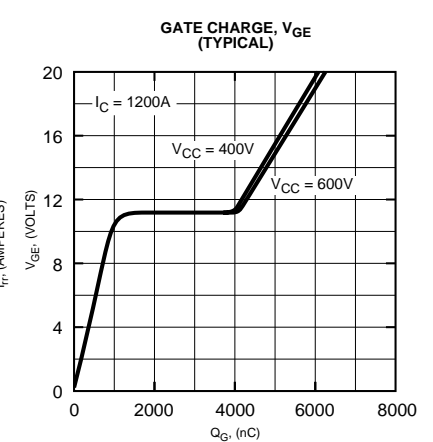
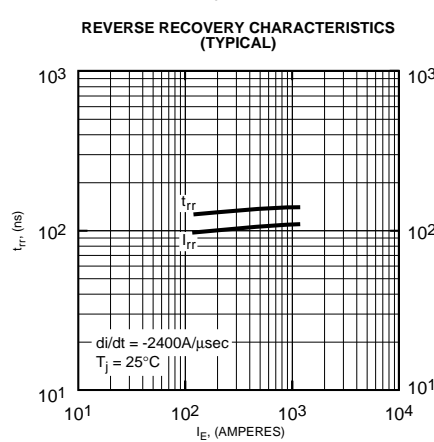
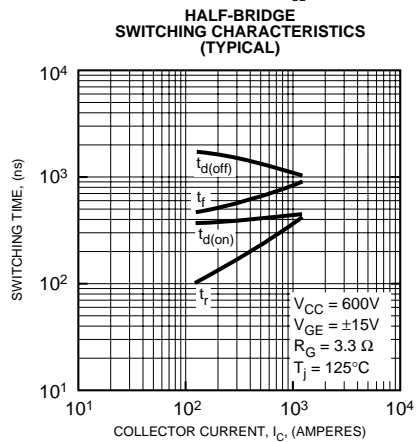
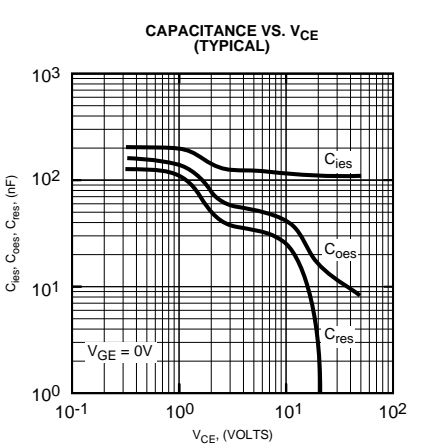
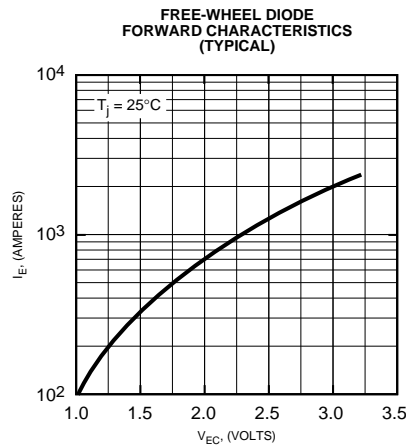
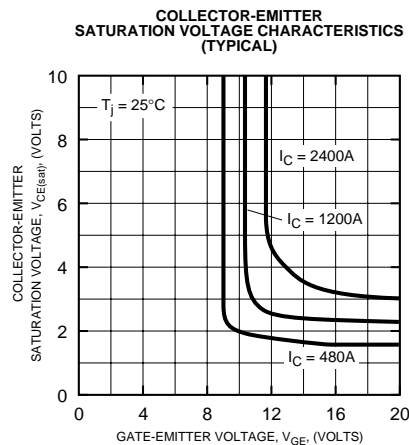
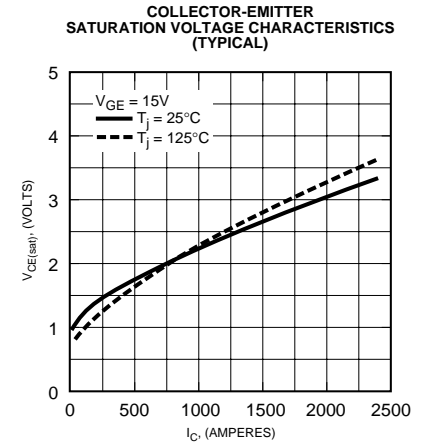
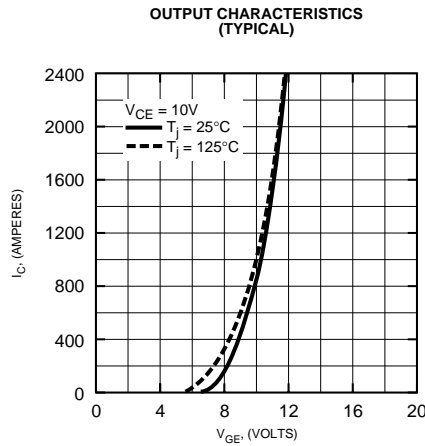
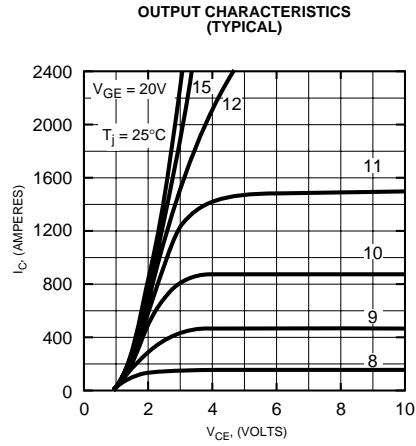
* Pulse width and repetition rate should be such that device junction temperature (T_j) does not exceed $T_{j(max)}$ rating.

**Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).



Powerex, Inc., 200 Hillis Street, Youngwood, Pennsylvania 15697-1800 (724) 925-7272

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